

IN THE SPECIFICATION

After the Title, please insert the following sub-heading and paragraph:

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is a continuation of and claims priority to United States Patent Application No. 09/736,157 entitled "PIN ALLOY-SEMICONDUCTOR, RADIATION DETECTORS WITH RECTIFYING JUNCTION CONTACTS, METHODS AND SYSTEMS FOR FORMING PIN ALLOY-SEMICONDUCTOR DEVICES WITH RECTIFYING JUNCTION CONTACTS, AND SYSTEMS AND METHODS FOR ANALYZING ALLOY-SEMICONDUCTOR PROPERTIES."

Please replace the ABSTRACT with the following paragraph:

The present invention pertains to a more efficient system and method for forming rectifying junction contacts in PIN alloy-semiconductor devices using photoelectrical and chemical etching. The present invention provides a means of creating rectifying junction contacts on alloy-semiconductor devices such as CdTe and CdZnTe, among others. In addition, the present invention also provides a simple and low cost method for revealing wafer surface morphology of alloy-semiconductors, thus providing an efficient and effective means for selecting single grain semiconductor substrates. Further, the present invention provides radiation detectors employing such alloy-semiconductor devices having improved rectifying junctions as the detector element.